

CAT93C46/CAT93C46I

1K-Bit SERIAL E2PROM

FEATURES

- High Speed Operation: 1MHz
- **Low Power CMOS Technology**
- Single 5V Supply
- 64 x 16 or 128 x 8 Selectable Serial Memory
- Self-Timed Write Cycle with Auto-Clear
- Hardware and Software Write Protection
- Power-Up Inadvertant Write Protection
- 100,000 Program/Erase Cycles
- 100 Year Data Retention
- Optional High Endurance Device Available

DESCRIPTION

The CAT93C46 and CAT93C46I are 1K bit Serial E²PROM memory devices which can be configured as either 64 registers by 16 bits (ORG pin at V_{CC)} or 128 registers by 8 bits (ORG pin at GND). Each register can be written (or read) serially by using the DI (or DO) pin. The CAT93C46/CAT93C46I is manufactured using

PIN CONFIGURATION

DIP Pac	:kage	SO Package J				
CS [•1 2 DI [3 DO [4	8	NC [•1 Vcc [2 cs [3 sk [4	8			
		<u> </u>				

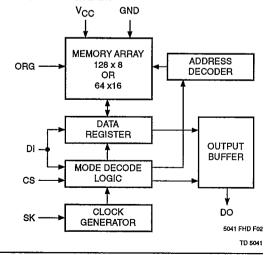
SO Package S SO Package K CS r □ Vcc cs 🚅 8 8 تع∨ ت ₽ NC SK 🗀 2 7 sk ⊏ 2 7 р ис 6 DI 3 D ORG DI 🗀 3 6 ORG 5 j GND DO C DO GND

PIN FUNCTIONS

Pin Name	Function			
cs	Chip Select			
SK	Clock Input			
DI	Serial Data Input			
DO	Serial Data Output			
Vcc	+5V Power Supply			
GND	Ground			
NC	No Connection			
ORG	Memory Organization			

Note: When the ORG pin is connected to V_{CC} , the 64 x 16 organization is selected. When it is connected to ground, the 128 x 8 organization is selected. If the ORG pin is left unconnected, then an internal pullup device will select the 64 x 16 organization.

BLOCK DIAGRAM



5041 FHD F01

ABSOLUTE MAXIMUM RATINGS*

Temperature Under Bias–55°C to +125°	C
Storage Temperature65°C to +150°	Ċ
Voltage on any Pin with Respect to Ground ⁽¹⁾ 2.0V to +V _{CC} +2.0	٥V
Vcc with Respect to Ground2.0V to +7.0	V
Package Power Dissipation Capability (Ta = 25°C)1.0	W
Lead Soldering Temperature (10 secs)300°	Ò,
Output Short Circuit Current ⁽²⁾ 100 m	ıΑ

*COMMENT

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions outside of those listed in the operational sections of this specification is not implied. Exposure to any absolute maximum rating for extended periods may affect device performance and reliability.

RELIABILITY CHARACTERISTICS

Symbol	Parameter	Min.	Max.	Units	Reference Test Method
N _{END} (3)	Endurance	100,000		Cycles/Byte	MIL-STD-883, Test Method 1033
T _{DR} (3)	Data Retention	100		Years	MIL-STD-883, Test Method 1008
V _{ZAP} (3)	ESD Susceptibility	2000		Volts	MIL-STD-883, Test Method 3015
I _{LTH} (3)(4)	Latch-Up	100		mA	JEDEC Standard 17

D.C. OPERATING CHARACTERISTICS

CAT93C46 T_A = 0°C to +70°C, V_{CC} = +5V±10%, unless otherwise specified. CAT93C46I $T_A = -40$ °C to +85°C, $V_{CC} = +5V\pm10\%$, unless otherwise specified.

			Limits		Units	Test Conditions
Symbol	Parameter	Min.	Тур.	Max.		
lcc ₁	Power Supply Current (Operating)		·	3	mA	DI = 0.0V, SK = 5.0V V _{CC} = 5.0V, CS = 5.0V, Output Open
lcc2	Power Supply Current (Standby)			100	μА	V _{CC} = 5.5V, CS = 0V DI = 0V SK = 0V
ILI	Input Leakage Current			2	μΑ	V _{IN} = 0V to 5.5V
llo	Output Leakage Current (Including ORG Pin)			10	μА	V _{OUT} = 0V to 5.5V, CS = 0V
VIH	High Level Input Voltage	2.0		Vcc + 1	V	
VIL	Low Level Input Voltage	-0.1		0.8	V	
VoH	High Level Output Voltage	2.4			V	I _{OH} = -400µA
V _{OL}	Low Level Output Voltage	• .		0.4	V	I _{OL} = 2.1mA

(2) Output shorted for no more than one second. No more than one output shorted at a time.

(3) This parameter is tested initially and after a design or process change that affects the parameter.

⁽¹⁾ The minimum DC input voltage is -0.5V. During transitions, inputs may undershoot to -2.0V for periods of less than 20 ns. Maximum DC voltage on output pins is V_{CC} +0.5V, which may overshoot to V_{CC} +2.0V for periods of less than 20 ns.

⁽⁴⁾ Latch-up protection is provided for stresses up to 100 mA on address and data pins from -1V to VCC +1V.

INSTRUCTION SET

			Address		Data			
Instruction	Start Bit	Opcode	128 x 8	64 x 16	128 x 8	64 x 16	Comments	
READ	1	1 0	A6-A0	A5-A0.	7		Read Address AN-A0	
ERASE	1	11	A6-A0	A5A0			Clear Address AN-A0	
WRITE	1	0 1	A6-A0	A5-A0	D7D0	D15-D0	Write Address AN-A0	
EWEN	1	0 0	11XXXXX	11XXXX			Write Enable	
EWDS	1	0 0	00XXXXX	00XXXX			Write Disable	
ERAL	1	0 0	10XXXXX	10XXXX			Clear All Addresses	
WRAL	1	0 0	01XXXXX	01XXXX	D7-D0	D15-D0	Write All Addresses	

A.C. CHARACTERISTICS

CAT93C46 T_A= 0°C to +70°C, V_{CC} = +5V±10%, unless otherwise specified. CAT93C46I T_A= -40°C to +85°C, V_{CC} = +5V±10%, unless otherwise specified.

			Limits			
Symbol	Parameter	Min.	Тур.	Max.	Units	Test Conditions
tcss	CS Setup Time	50			ns	
tcsH	CS Hold Time	0			ns	
t _{DIS}	DI Setup Time	100			ns	C _L = 100pF
t _{DIH}	DI Hold Time	100			ns	V _{OL} = 0.8V, V _{OH} = 2.0V
t _{PD1}	Output Delay to 1			500	ns	$V_{IL} = 0.45V, V_{IH} = 2.4V$
t _{PD0}	Output Delay to 0			500	ns	1
tHZ ⁽³⁾	Output Delay to High-Z			100	ns	
t _{EW}	Program/Erase Pulse Width			10	ms	
tcsmin	Minimum CS Low Time	250			ns	
tskHi	Minimum SK High Time	100			ns	
tsklow	Minimum SK Low time	660			ns	
tsv	Output Delay to Status Valid			500	ns	C _L = 100pF
SK _{MAX}	Maximum Clock Frequency	DC		1	MHz	

⁽³⁾ This parameter is tested initially and after a design or process change that affects the parameter.

DEVICE OPERATION

The CAT93C46/CAT93C46I is a 1024 bit nonvolatile memory intended for use with industry standard microprocessors. The CAT93C46/CAT93C46I can be organized as either 64 registers by 16 bits, or as 128 registers by 8 bits. Seven 9 bit instructions (10 bit instruction in 128 by 8 organization) control the reading, writing and erase operations of the device, The CAT93C46/CAT93C46I operates on a single 5V supply and will generate on chip, the high voltage required during any write operation.

Instructions, addresses, and write data are clocked into the DI pin on the rising edge of the clock (SK). The DO pin is normally in a high impedance state except when reading data from the device, or when checking the ready/busy status after a write operation.

The ready/busy status can be determined after a write

operation by selecting the device (CS high) and polling the DO pin: DO low indicates that the write operation is not completed, while DO high indicates that the device is ready for the next instruction. If necessary, the DO pin may be placed back into a high impedance state during chip select by shifting a dummy "1" into the DI pin. The DO pin will enter the high impedance state on the falling edge of the clock (SK). Placing the DO pin into the high impedance state is recommended in applications where the DI pin and the DO pin are to be tied together to form a common DI/O pin.

The format for all instructions sent to the CAT93C46/ CAT93C46l is a logical "1" start bit, a 2 bit (or 4 bit) op code, a 6 bit address (7 bit address when organized as 128 x 8), and for write operations a 16 bit data field (8 bit data field when organized as 128 x 8).

Figure 1. Sychronous Data Timing (5)

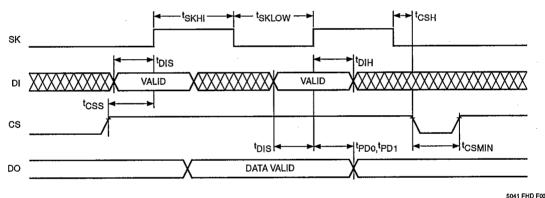
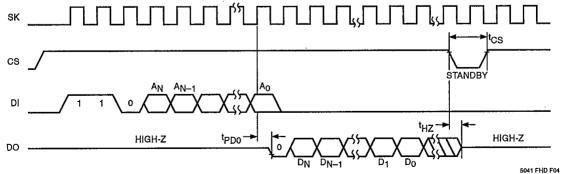


Figure 2. Read Instruction Timing (5)



Note

⁽⁵⁾ The ORG pin is used to configure the device for x8 or x16 operation. When x8 organization is selected, AN = A6 and DN = D7. When x16 organization is selected, AN = A5 and DN = D15.

CAT93C46/CAT93C46I

At power-down, when Vcc falls below a threshold of approximately 3.5V, the data protection circuitry inhibits the erase and write instructions and a write disable (EWDS) is executed internally.

NOTE: This device will accept a start bit that is generated when both SK and DI are high with respect to a low to high transition of CS.

Read

Upon receiving a READ command and an address (clocked into the DI pin), the DO pin of the CAT93C46/ CAT93C46I will come out of the high impedance state and, after sending an initial dummy zero bit, will begin shifting out the data addressed. The output data bits will toggle on the rising edge of the SK clock and are stable after the specified time delay (teno or tena).

Write

After receiving a WRITE command, address and the

data, the CS (chip select) pin must be deselected for a minimum of 250ns (tcsmin). The falling edge of CS will start the self clocking clear and data store cycle of the memory location specified in the instruction. The clocking of the SK pin is not necessary after the device has entered the self clocking mode. The ready/busy status of the CAT93C46/CAT93C46I can be determined by selecting the device and polling the DO pin. Since this device features Auto-Clear before write, it is NOT necessary to erase a memory location before the WRITE command is sent.

Erase

Upon receiving an ERASE command and address, the CS (chip select) pin must be deselected for a minimum of 250ns (tcsmin). The falling edge of CS will start the self clocking clear cycle of the memory location specified in the instruction. The clocking of the SK pin is not necessary after the device has entered the self clocking mode. The ready/busy status of the CAT93C46/CAT93C46I



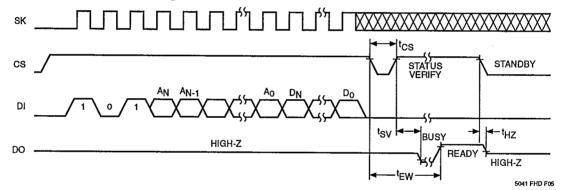
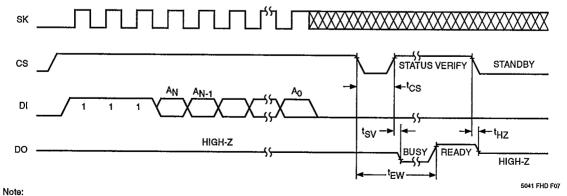


Figure 4. Erase Instruction Timing (5)



(5) The ORG pin is used to configure the device for x8 or x16 operation. When x8 organization is selected, AN = A6 and DN = D7. When x16 organization is selected, AN = A5 and DN = D15.

can be determined by selecting the device and polling the DO pin. Once cleared, the content of a cleared location returns to a logical "1" state.

Erase/Write Enable and Disable

The CAT93C46/CAT93C46I powers up in the write disable state. Any writing after power-up or after an EWDS (write disable) instruction must first be preceded by the EWEN (write enable) instruction. Once the write instruction is enabled, it will remain enabled until power to the device is removed, or the EWDS instruction is sent. The EWDS instruction can be used to disable all CAT93C46/CAT93C46I write and clear instructions, and will prevent any accidental writing or clearing of the device. Data can be read normally from the device regardless of the write enable/disable status.

Erase All

Upon receiving an ERAL command, the CS (chip select) pin must be deselected for a minimum of 250ns (tosміл). The falling edge of CS will start the self clocking clear cycle of all memory locations in the device. The clocking of the SK pin is not necessary after the device has entered the self clocking mode. The ready/busy status of the CAT93C46/CAT93C46I can be determined by selecting the device and polling the DO pin. Once cleared, the contents of all memory bits return to a logical "1" state.

Write All

Upon receiving a WRAL command and data, the CS (chip select) pin must be deselected for a minimum of 250ns (tcsmin). The falling edge of CS will start the self clocking data write to all memory locations in the device. The clocking of the SK pin is not necessary after the device has entered the self clocking mode. The ready/ busy status of the CAT93C46/CAT93C46I can be determined by selecting the device and polling the DO pin. It IS necessary for all memory locations to be cleared before the WRAL command is executed.

Figure 5. EWEN/EWDS Instruction Timing (5)

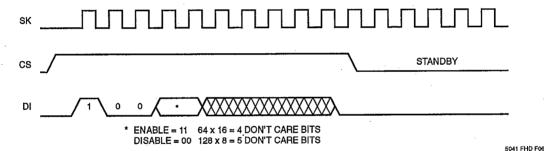
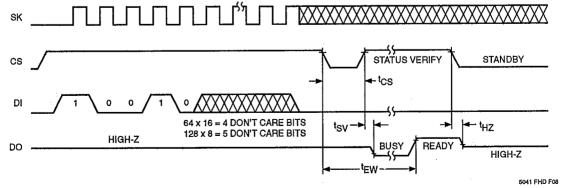


Figure 6. ERAL Instruction Timing (5)



Note:

⁽⁵⁾ The ORG pin is used to configure the device for x8 or x16 operation. When x8 organization is selected, AN = A6 and DN = D7. When x16 organization is selected, AN = A5 and DN = D15.

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Start Bit Timing

The CAT93C46/CAT93C46I features an alternate start bit timing where the device will accept a start bit that is generated when both SK and DI are high with respect to a low to high transition of CS (see Figure 8). This allows

the user to send instructions from microprocessors that transmit and receive data using a sequence of 8 clock cycles only. Once this start bit is generated all subsequent data is clocked into the device on the positive clock edge of SK.

Figure 7. WRAL Instruction Timing (5)

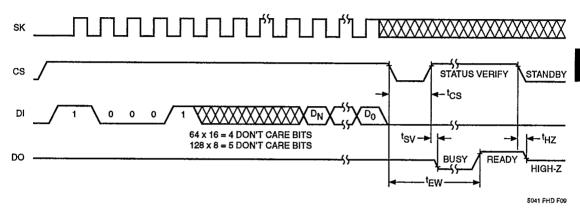
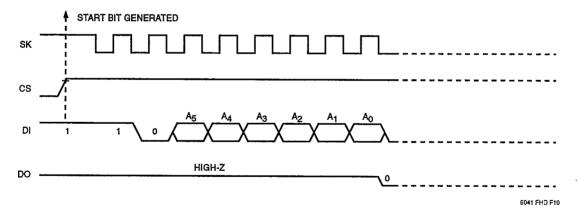


Figure 8. Alternate Start Bit Timing Example: Read Instruction (x 16) (5)



Note:

⁽⁵⁾ The ORG pin is used to configure the device for x8 or x16 operation. When x8 organization is selected, AN = A6 and DN = D7. When x16 organization is selected, AN = A5 and DN = D15.